COMPLEMENTARY SILICON POWER TRANSISTORS

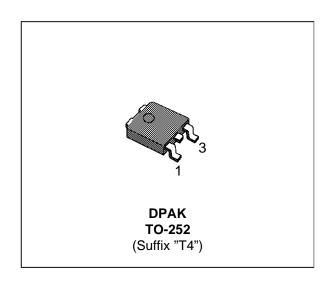
- SGS-THOMSON PREFERRED SALESTYPES
- SURFACE-MOUNTING TO-252 (DPAK)
 POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICAL SIMILAR TO MJE2955 AND MJE3055

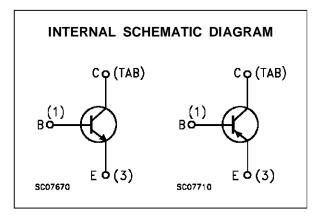
APPLICATIONS

 GENERAL PURPOSE SWITCHING AND AMPLIFIER TRANSISTORS

DESCRIPTION

The MJD2955 and MJD3055 form complementary NPN-PNP pairs. They are manufactured using Epitaxial Base technology for cost-effective performance.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	60	V
V _{CEO} Collector-Emitter Voltage (I _B = 0)		70	V
V _{EBO} Emitter-Base Voltage (I _C = 0)		5	V
I _C Collector Current		10	А
Ι _Β	Base Current	6	А
P_{tot}	Total Dissipation at T _c = 25 °C	20	W
T _{stg}	Storage Temperature	-65 to 150	°C
T _j Max. Operating Junction Temperature		150	°C

For PNP type voltage and current values are negative.

January 1995 1/6

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	6.25	°C/W	
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	100	°C/W	

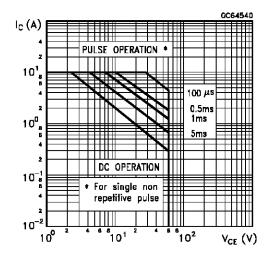
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ICEX	Collector Cut-off Current ()	$V_{CB} = 70 \text{ V}$ $V_{BE} = -1.5 \text{V}$ $V_{CB} = 70 \text{ V}$ $V_{BE} = -1.5 \text{V}$ $V_{CB} = 150 ^{\circ}\text{C}$			0.2 2	μA μA
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = 70 \text{ V}$ $V_{CB} = 70 \text{ V}$ $T_j = 150 \text{ °C}$			0.2 2	μA μA
I _{CEO}	Collector Cut-off Current (i _B = 0)	V _{CB} = 30 V			50	μА
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			0.5	mA
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 30 mA	60			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = 4 \text{ A}$ $I_B = 0.4 \text{ A}$ $I_C = 10 \text{ A}$ $I_B = 3.3 \text{ A}$			1.1 8	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 4 A V _{CE} = 4 V			1.8	V
h _{FE} *	DC Current Gain	I _C = 4 A	20 5		100	
f⊤	DC Current Gain	I _C = 0.5 A V _{CE} = 10 V f = 500 KHz	2			MHz

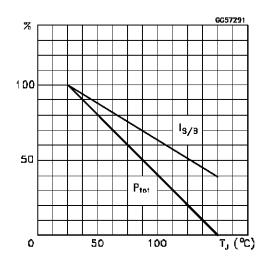
^{*} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

For PNP type voltage and current values are negative.

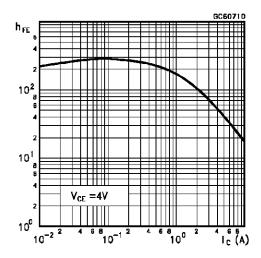
Safe Operating Areas



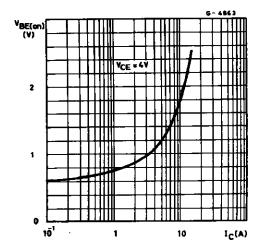
Derating Curve



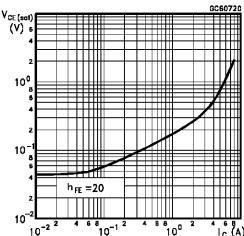
DC Current Gain (NPN type)



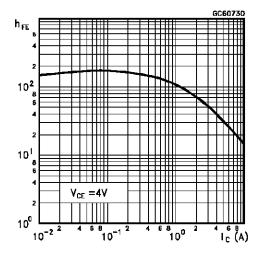
DC Transconductance (NPN type)



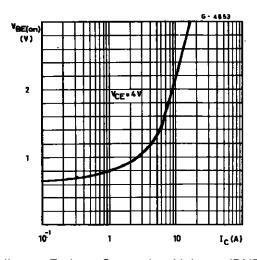
Collector-Emitter Saturation Voltage (NPN type)



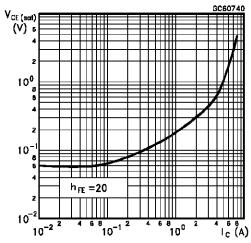
DC Current Gain (PNP type)



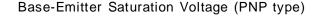
DC Transconductance (PNP type)

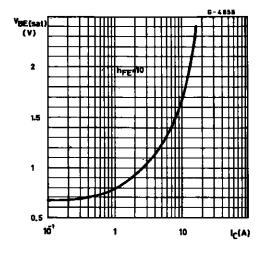


Collector-Emitter Saturation Voltage (PNP type)

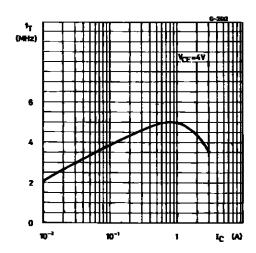


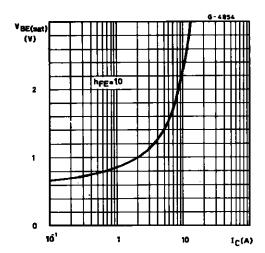
Base-Emitter Saturation Voltage (NPN type)



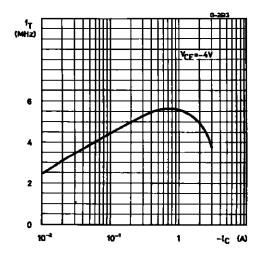


Transition Frequency (NPN types)



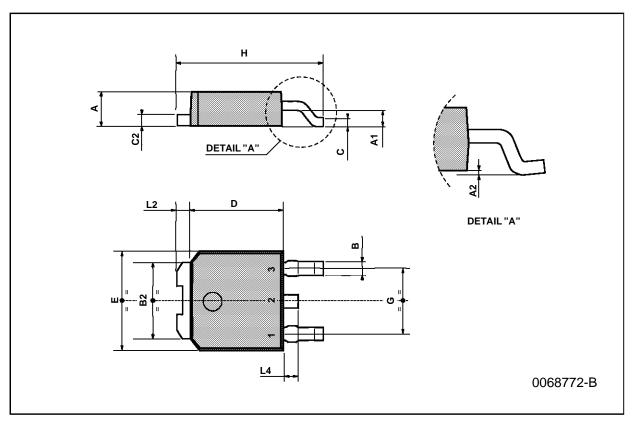


Transition Frequency (PNP types)



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	2.2		2.4	0.086		0.094	
A1	0.9		1.1	0.035		0.043	
A2	0.03		0.23	0.001		0.009	
В	0.64		0.9	0.025		0.035	
B2	5.2		5.4	0.204		0.212	
С	0.45		0.6	0.017		0.023	
C2	0.48		0.6	0.019		0.023	
D	6		6.2	0.236		0.244	
E	6.4		6.6	0.252		0.260	
G	4.4		4.6	0.173		0.181	
Н	9.35		10.1	0.368		0.397	
L2		0.8			0.031		
L4	0.6		1	0.023		0.039	



MJD2955 MJD3055

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